

## **Application Data Sheet**

### **Application Information**

Application Type::	Regular
Subject Matter::	Utility
Suggested Group Art Unit::	N/A
CD-ROM or CD-R?::	None
Sequence submission?::	None
Computer Readable Form (CRF)?::	No
Title::	MULTILEVEL SEMICONDUCTOR MEMORY, WRITE/READ METHOD THERETO/THEREFROM AND STORAGE MEDIUM STORING WRITE/READ PROGRAM
Attorney Docket Number::	21737-00013-US4
Request for Early Publication?::	No
Request for Non-Publication?::	No
Total Drawing Sheets::	10
Small Entity?::	No
Petition included?::	No
Secrecy Order in Parent Appl.?::	No

### **Applicant Information**

Applicant Authority Type::	Inventor
Primary Citizenship Country::	Japan
Status::	Full Capacity
Given Name::	Katsuki
Family Name::	Hazama
City of Residence::	Tokyo-to
Country of Residence::	Japan
Street of mailing address::	c/o Nippon Steel Corporation 6-3, Otemachi 2-chome

City of mailing address:: Chiyoda-ku, Tokyo-to  
State or Province of mailing address::  
Country of mailing address:: Japan

**Correspondence Information**

Correspondence Customer Number:: 30678

**Representative Information**

Representative Customer Number:: 30678

**Domestic Priority Information**

Application::	Continuity Type::	Parent Application::	Parent Filing Date::
This Application	Divisional of	09/438,295	11/12/1999
This Application	Divisional of	08/931,519	09/16/1997

**Foreign Priority Information**

Country::	Application number::	Filing Date::	Priority Claimed::
Japan	267844	09/18/96	Yes
Japan	342663	12/06/96	Yes

**Assignee Information**

Assignee name:: Nippon Steel Corporation  
6-3, Otemachi 2-chome  
Chiyoda-ku, Tokyo-to, JAPAN